

1. (Twice Amended)

Sub D1

A method of manufacturing a thin film resistor with a moisture barrier comprising:
depositing a metal film resistive layer on a thin film resistor substrate;
attaching a thin film resistor termination on each end of the metal film resistive layer; and
depositing the moisture barrier comprising a layer of tantalum pentoxide film directly overlaying
and attaching to the metal film resistive layer to reduce failures due to electrolytic
corrosion under powered moisture conditions.

15. (Amended)

Sub D2

A method of manufacturing a thin film resistor with a moisture barrier comprising:
depositing a metal film resistive layer on a substrate;
attaching a termination on each end of the metal film resistive layer;
depositing a passivation layer directly overlaying and attaching to the metal film layer; and
depositing the moisture barrier comprising a layer of tantalum pentoxide film directly overlaying
and attaching to the passivation layer for reducing failures due to electrolytic corrosion
under powered moisture conditions.